

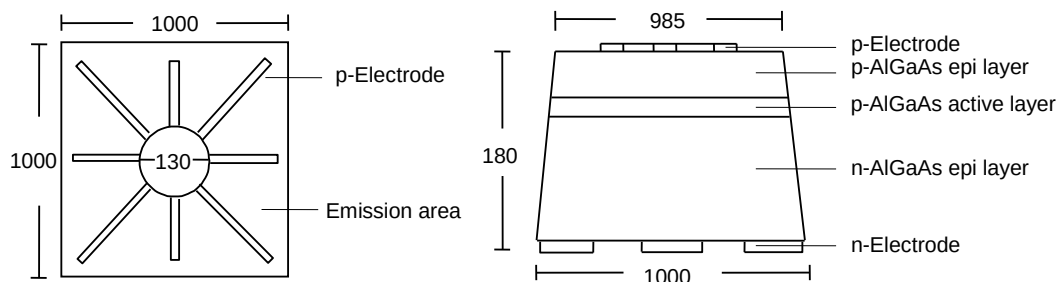
■ Features :

- AlGaAs/AlGaAs Wafer
- Very High Power
- High Speed
- Superior Thermal Stability

■ Typical Applications :

- IrDA
- Encoder
- Data Communication

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	1000 μm x 1000 μm
	Thickness	180 μm
	Emission area	985 μm
	Bonding pad	130 μm
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 100 \text{ mA}$	-	1.45	1.80	V
		$I_F = 350 \text{ mA}$	-	1.60	2.00	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_P	$I_F = 50 \text{ mA}$	-	810	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 50 \text{ mA}$	-	40	-	nm
Radiant Power	P_o	$I_F = 350 \text{ mA}$	20.0	30.0	-	mW
Rise / Fall Time	t_r / t_f	$I_F = 50 \text{ mA}$	-	25 / 15	-	ns

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

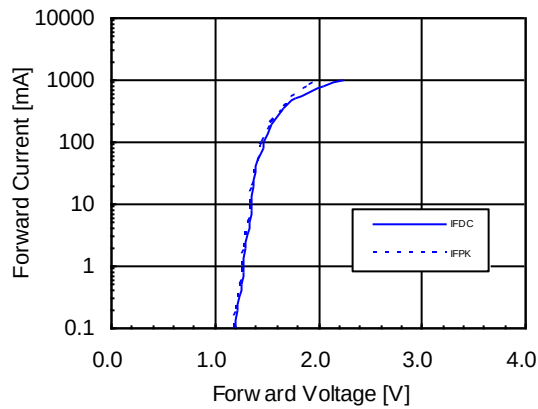


Fig 2. Relative Radiant Power vs. Wavelength

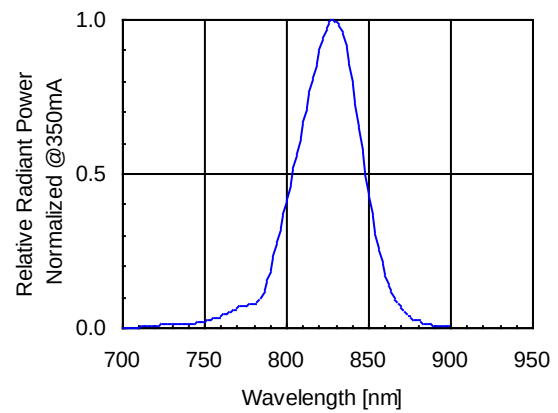


Fig 3. Relative Radiant Power vs. Forward DC Current

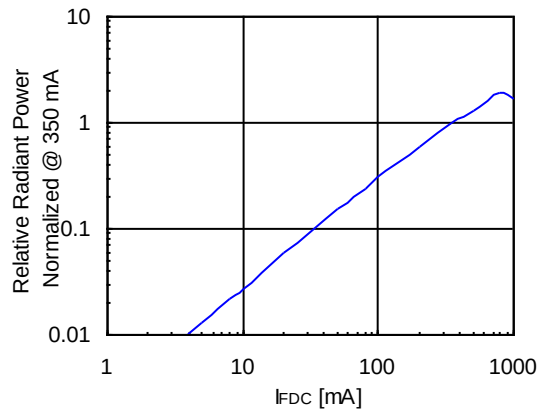


Fig 4. Relative Radiant Power vs. Forward Peak Current

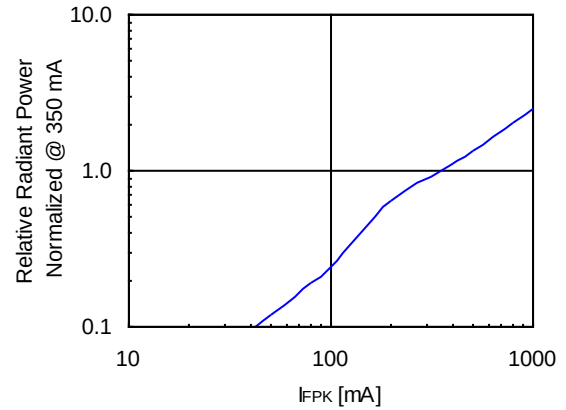


Fig 5. Forward DC Voltage vs. Temperature

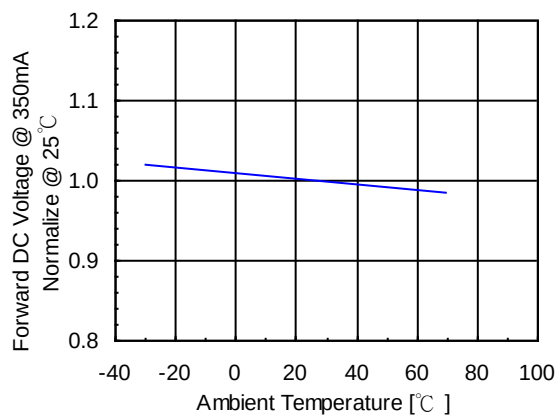


Fig 6. Relative Radiant Power vs. Temperature

